

BRDBC857

Rev.E Jul.-2024

描述 / Descriptions

SOT-363 塑封封装双 PNP 半导体三极管。Double silicon PNP transistor in a SOT-363 Plastic Package.

特征 / Features

高电压,与 BRDBC847 互补,无卤产品。

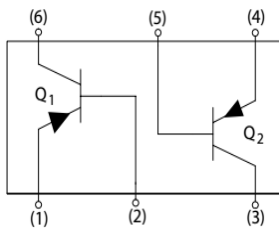
High voltage, complementary pair with BRDBC847, HF Product.

用途 / Applications

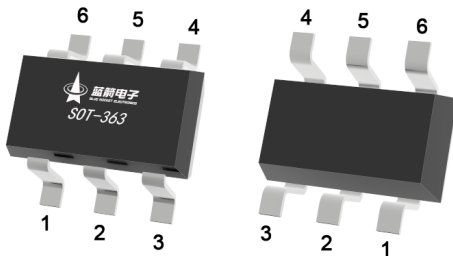
用于普通高压放大。

General purpose high voltage amplifier.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN 1、4 : Emitter

PIN 2、5 : Base

PIN 3、6 : Collector

放大及印章代码 / h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	A	B	C
h_{FE} Range	125~250	220~475	420~800
Marking	3E	3F	3G

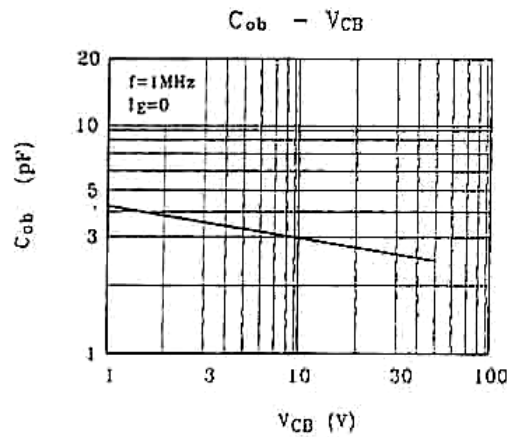
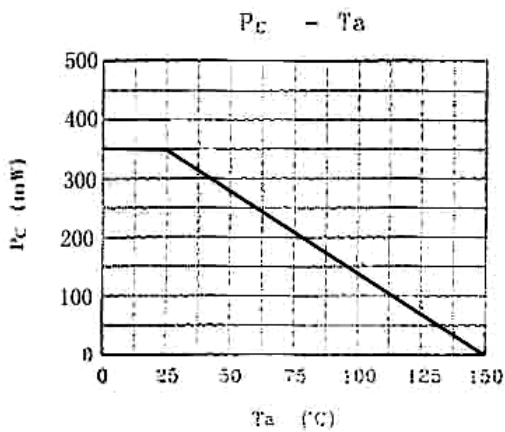
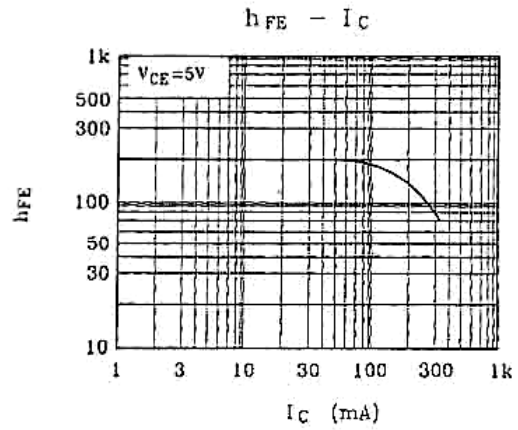
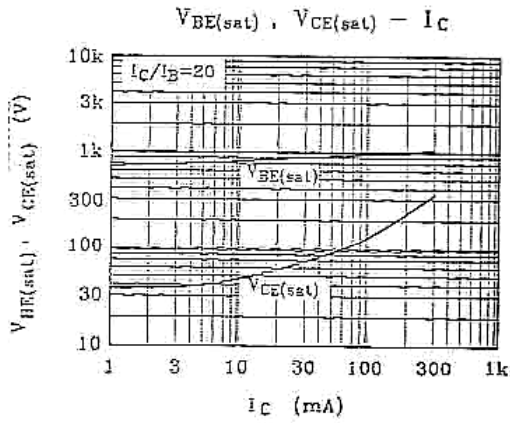
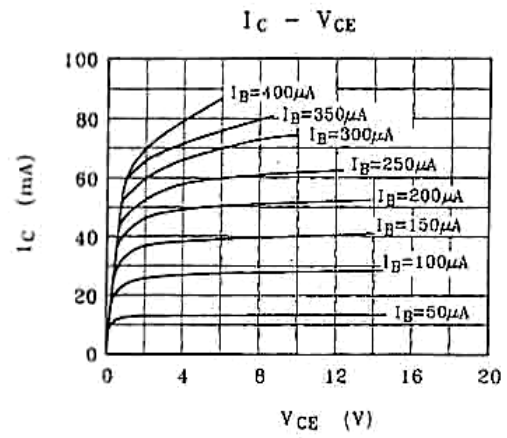
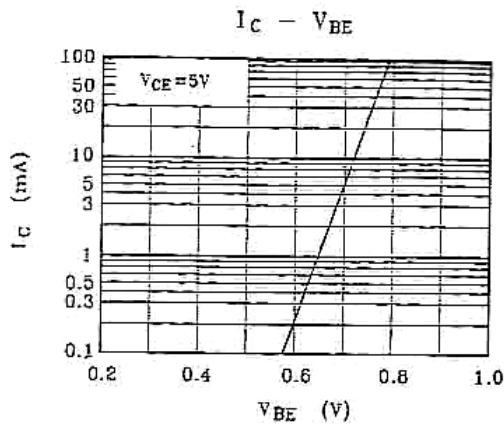
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V _{CBO}	-50	V
Collector to Emitter Voltage	V _{CEO}	-45	V
Emitter to Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-100	mA
Total Package Dissipation	P _D	380	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	328	°C/W
Junction Temperature	T _j	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

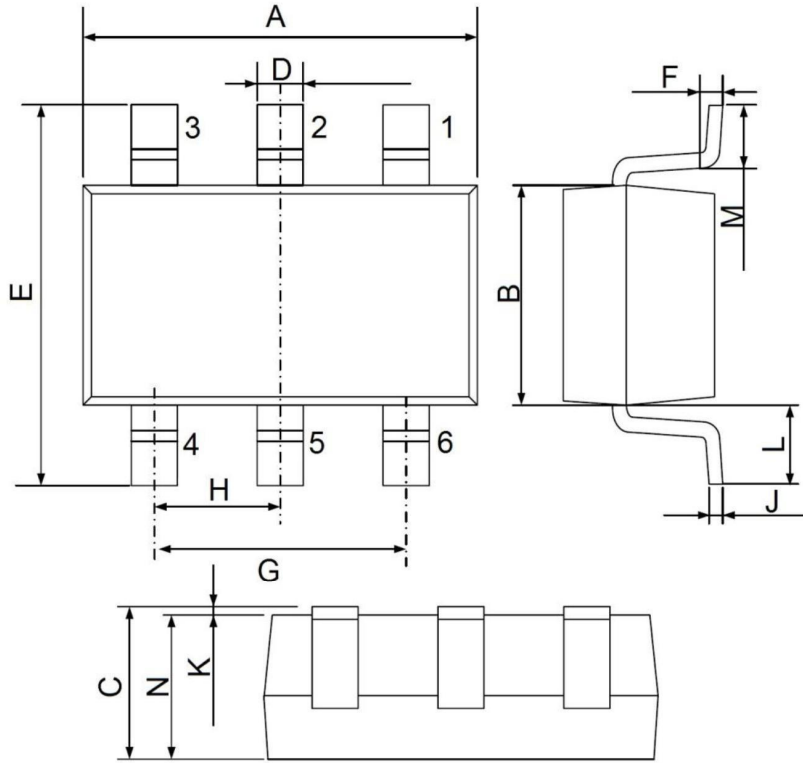
参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector-Base Breakdown Voltage	V _{CBO}	I _C = -10μA I _E = 0	-50			V
Collector-Emitter Breakdown Voltage	V _{CEO}	I _C = -10mA I _B = 0	-45			V
Emitter-Base Breakdown Voltage	V _{EBO}	I _E = -10μA I _C = 0	-5.0			V
Collector-Emitter Breakdown Voltage	V _{CES}	I _C = -10μA V _{EB} = 0	50			V
Collector Cut-Off Current	I _{CBO}	V _{CB} = -30V I _E = 0			-15	nA
		V _{CB} = -30V I _E = 0 T _A = 150°C			-4.0	μA
DC Current Gain	h _{FE}	V _{CE} = -5.0V I _C = -10μA		150		
		V _{CE} = -5.0V I _C = -2.0mA	125		800	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -10mA I _B = -0.5mA			-0.30	V
		I _C = -100mA I _B = -5.0mA			-0.65	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = -10mA I _B = -0.5mA		-0.70		V
		I _C = -100mA I _B = -5.0mA		-0.90		V
Base-Emitter Voltage	V _{BE(on)}	I _C = -2.0mA V _{CE} = -5.0V	-0.60		-0.75	V
		I _C = -10mA V _{CE} = -5.0V			-0.82	V
Transition Frequency	f _T	V _{CE} = -5.0V I _C = -10mA f = 100MHz	100			MHz
Output Capacitance	C _{ob}	V _{CB} = -10V f = 1.0MHz			4.5	pF
Noise Figure	NF	I _C = -0.2mA V _{CE} = -5.0V R _S = 2.0kΩ f = 1.0kHz BW = 200Hz			10	dB

电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

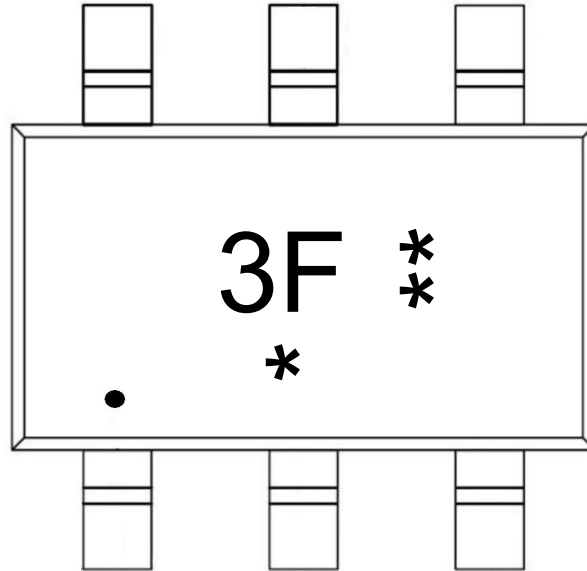
SOT-363-6L



UNIT: mm

DIM	MIN	MAX
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	1.95	2.25
F	0.20 Typ.	
G	1.20	1.40
H	0.65 Typ.	
J	0.08	0.15
K	0.00	0.10
L	0.525 Ref.	
M	0.26	0.46
N	0.90	1.10

印章说明 / Marking Instructions



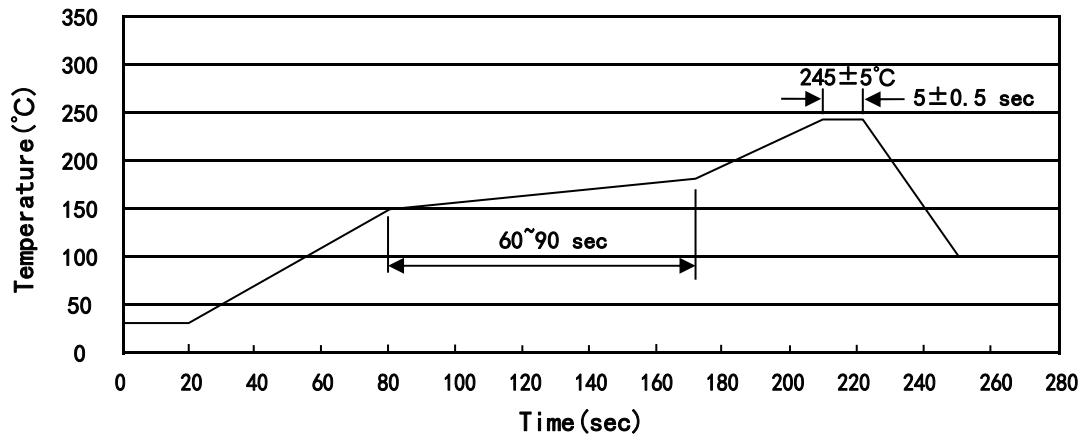
说明：

- ： 为“1”脚
- 3： 为型号代码
- F： 为 h_{FE} 档次代码
- ***： 为生产批号代码，随生产批号变化

Note:

- ： "1" Pin
- 3： Product Type Code
- F： h_{FE} Classifications Symbol Code
- ***： Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-363	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices